

09/856966

JC12 Rec'd PCT/PTO 25 MAY 2001

<b>PTO-1449 (Modified)</b>  <b>U.S. DEPARTMENT OF COMMERCE</b> <b>PATENT AND TRADEMARK OFFICE</b>  <b>INFORMATION DISCLOSURE STATEMENT</b> <b>BY APPLICANT</b>	<b>Attorney Docket No.:</b> UNVN.62457	<b>Serial Number: (International)</b> <b>#6</b> PCT/US99/28038 <b>3-7-02</b> <b>DRS</b>
	<b>Applicant:</b> DOWBEN, Peter et al.	
	<b>Filing Date:</b>	<b>Group:</b>

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EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
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	<b>Applicant:</b> Peter Dowben, et al.	
	<b>Filing Date:</b> September 6, 2001	<b>Group:</b> 3641

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## FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

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